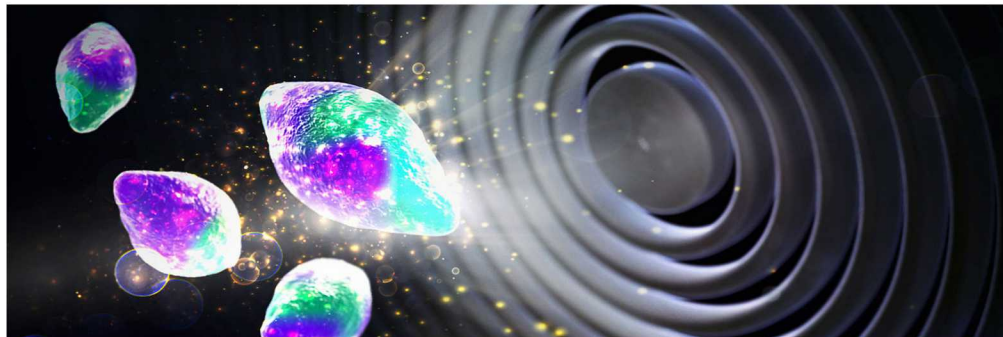


Electrochemical ion insertion for energy storage and neuromorphic computing



PRESENTED BY

Yiyang Li

This work is supported by the Sandia National Laboratories Truman Fellowship Program, which is funded by the Laboratory Directed Research and Development (LDRD) Program. Sandia National Laboratories is a multi-mission laboratory managed and operated by National Technology and Engineering Solutions of Sandia, LLC, a wholly owned subsidiary of Honeywell International Inc., for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-NA-0003525.



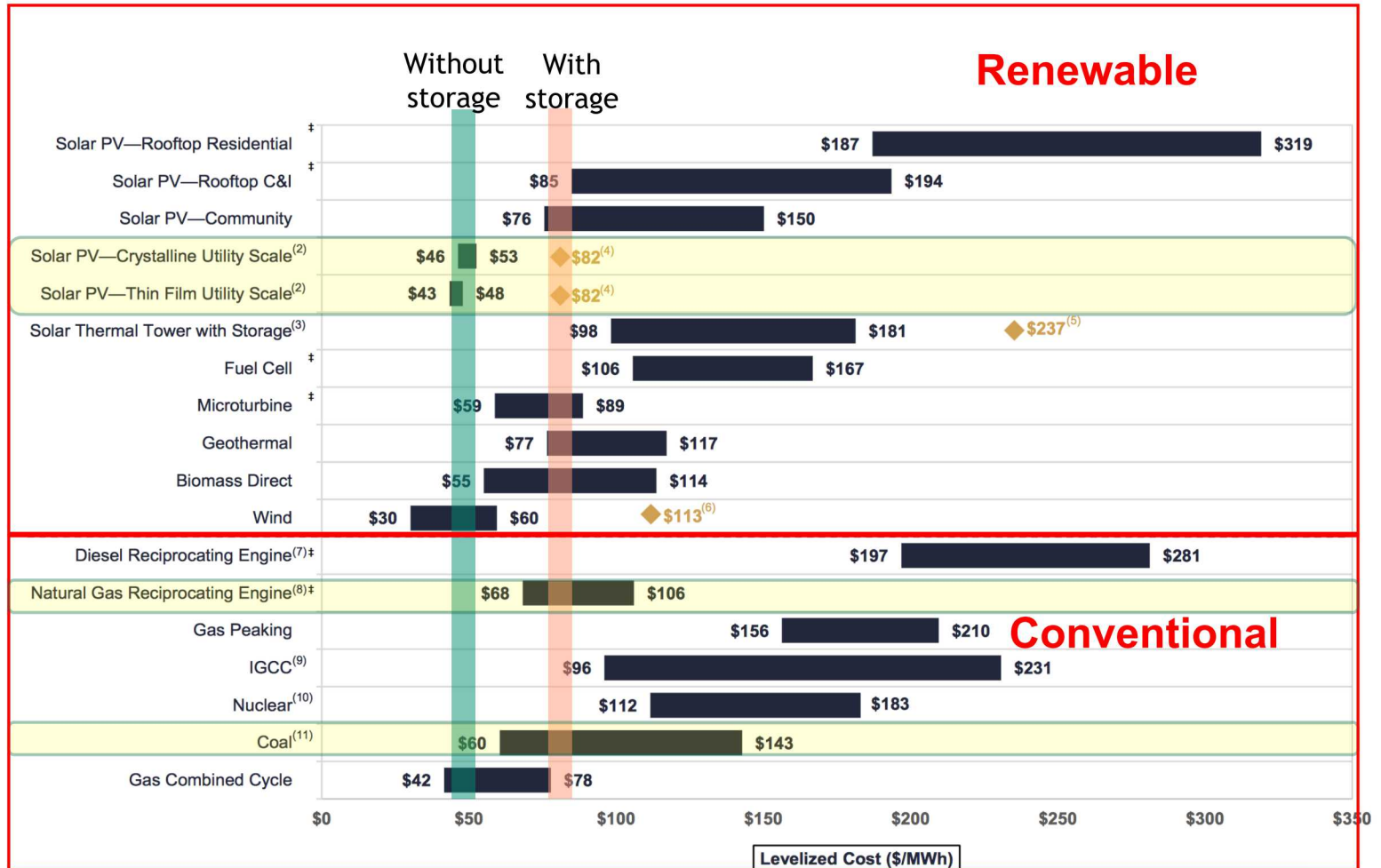
Sandia National Laboratories is a multi-mission laboratory managed and operated by National Technology and Engineering Solutions of Sandia, LLC, a wholly owned subsidiary of Honeywell International Inc. for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-NA0003525.



7 billion people
16 Terawatt of Power Consumed



Renewable electricity is cost-effective today



Storage: the key to enabling renewable energy to be used when and where we use it



Energy storage in personal transportation

Honda Clarity, Electric



90g CO₂ /mile
\$0.03 / mile

Honda Accord, Gasoline



300g CO₂ / mile
\$0.10 / mile

Electricity: \$0.13/kWh, 300g CO₂ /kWh (SF Bay area), 4 miles/kWh
Gasoline: \$3.00/gallon, 9000g CO₂/gallon, 30 miles/gallon

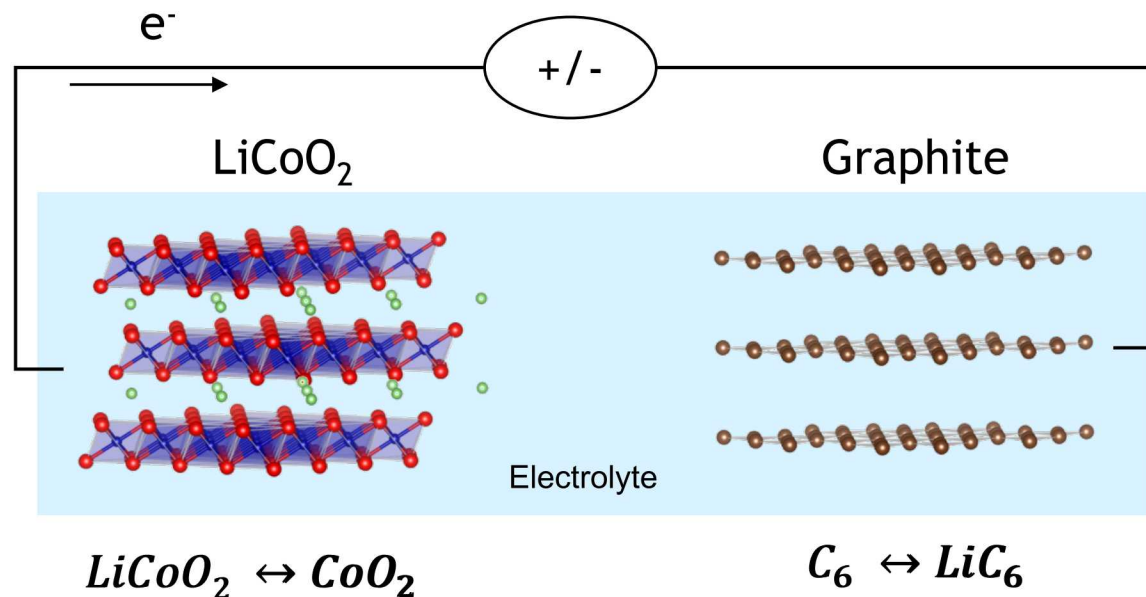
Source: Honda, Tesla





Electrochemical ion insertion

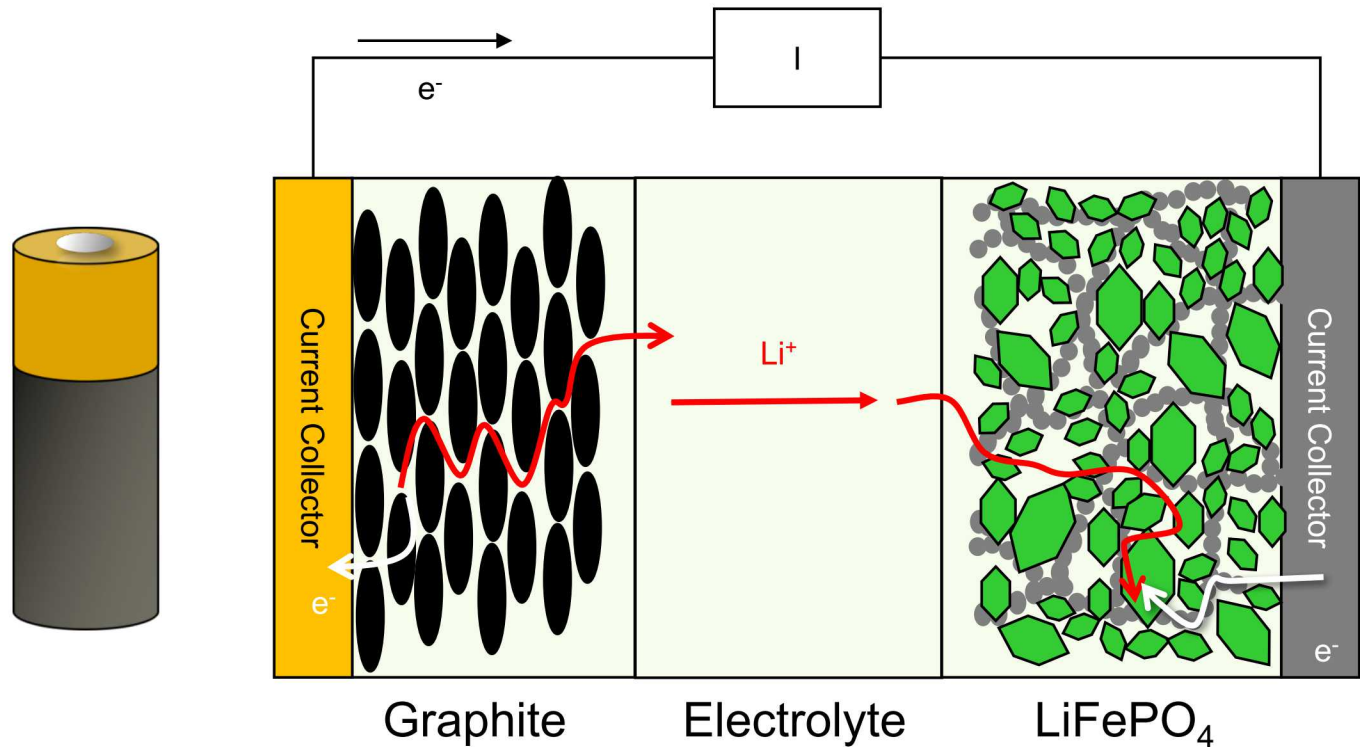
Using electrical signals to dynamically control material composition



Modulating the material composition through current and voltage.
Alter solid-state chemistry through electronic signals



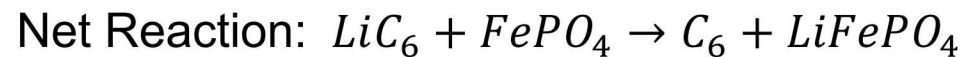
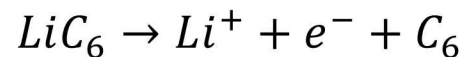
Ion insertion in a Li-ion battery



$$Energy = QV$$

$$Q = e n_{Li}$$

$$V = \frac{\Delta G_{rxn}}{e}$$



$$\Delta G = -320 \frac{kJ}{mol}$$

$$V = -\frac{\Delta G}{nFe} = 3.4 V$$

Discharge: inserting Li into Li_xFePO_4

Charge: removing Li from Li_xFePO_4

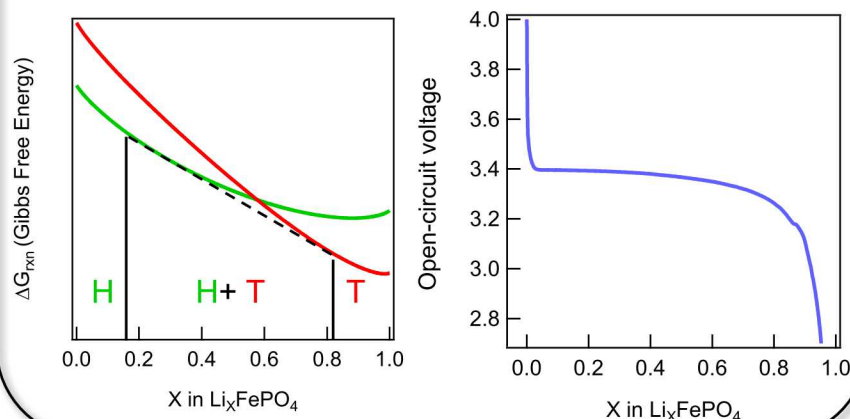
C-rate: current to (dis)charge in 1 hr

2C: 30 min (dis)charge



Phase separation in Li_xFePO_4

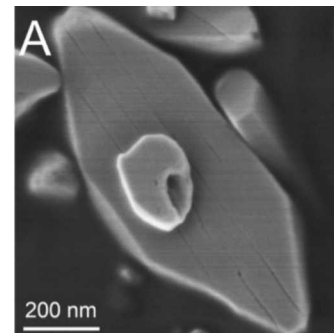
Large miscibility gap



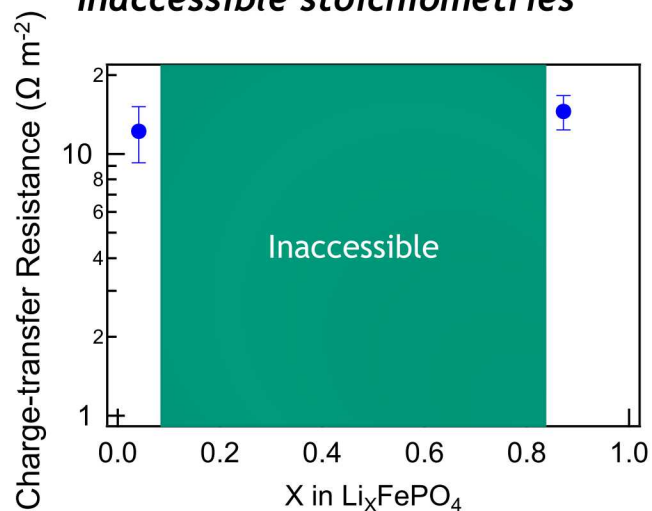
Consequences of phase separation

Mechanical strain

Yu et al. *Nano Lett.* (2015)



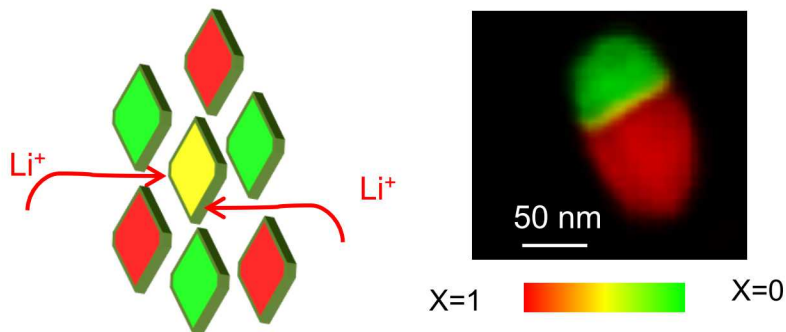
Inaccessible stoichiometries



Phase separation

Inter-particle

Intra-particle



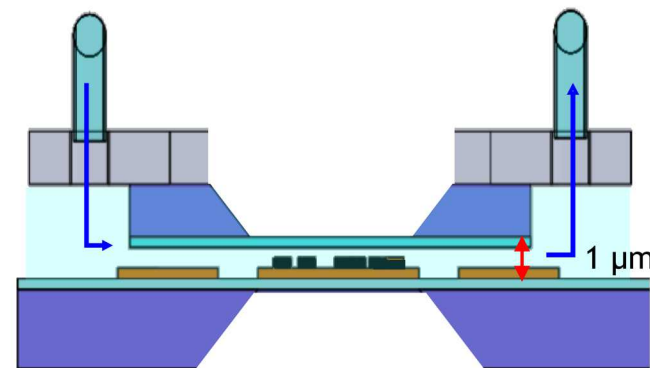
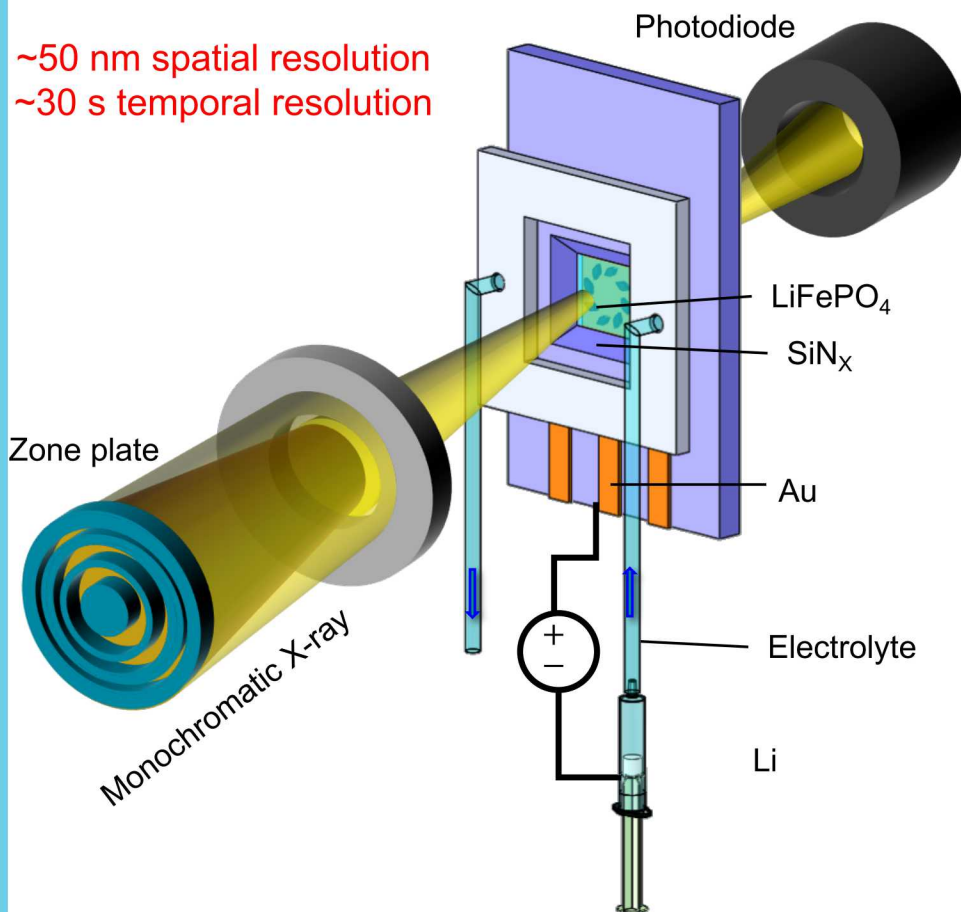
Y. Li et al. *Nature Mater.* **13**, 1149-56 (2014)

Goal: identify how to control phase separation

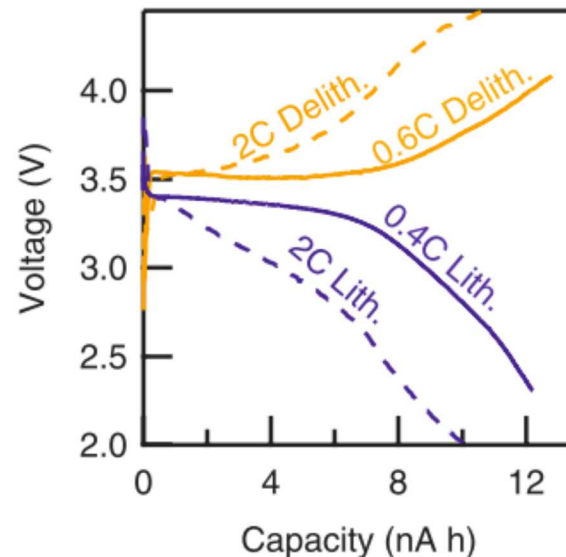


Visualizing battery (dis)charge using in situ X-ray microscopy

Tracking lithium insertion during cycling



Robust electrochemical cycling

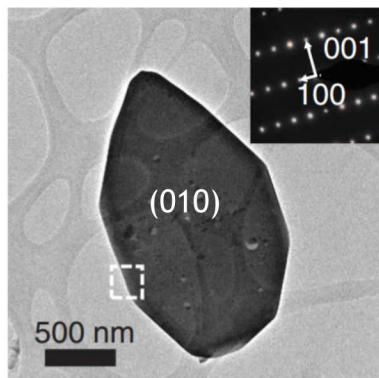


J. Lim*, Y. Li*, et al. *Science*, **353**, 566-571 (2016)

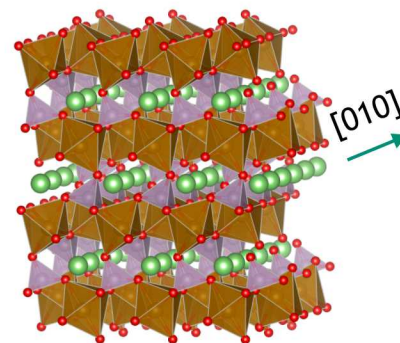
*equal contribution authors



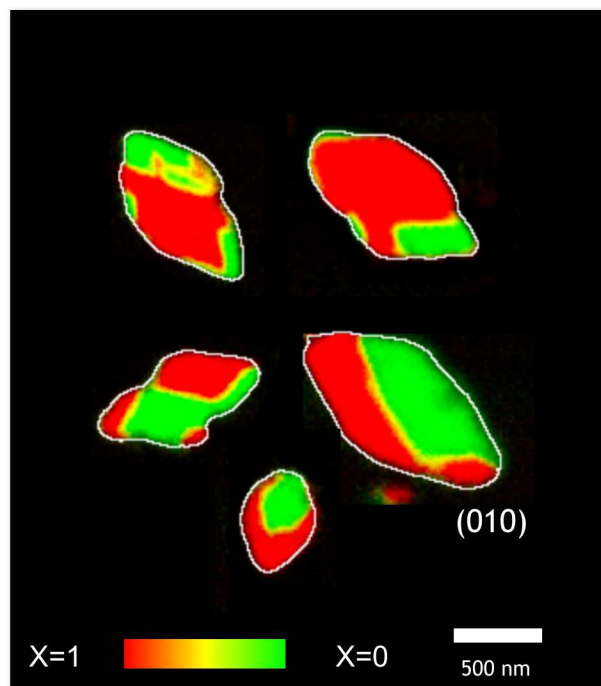
Tracking lithium insertion within particles *in situ*



100-nm thick single crystalline particles



One dimensional lithium conductor



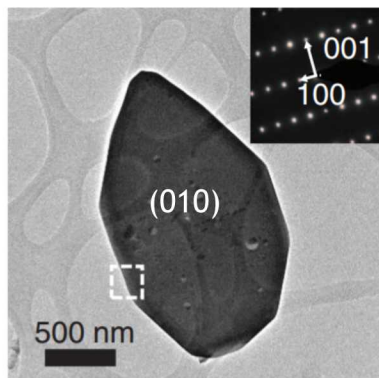
Equilibrium & slow rates

J. Lim*, Y. Li*, et al. *Science*, **353**, 566-571 (2016)

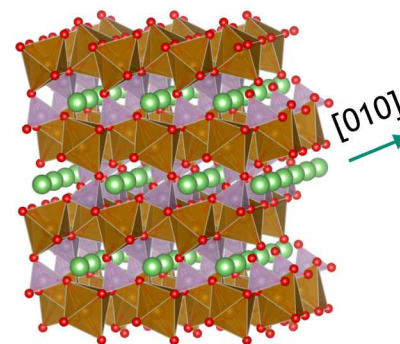
*equal contribution authors



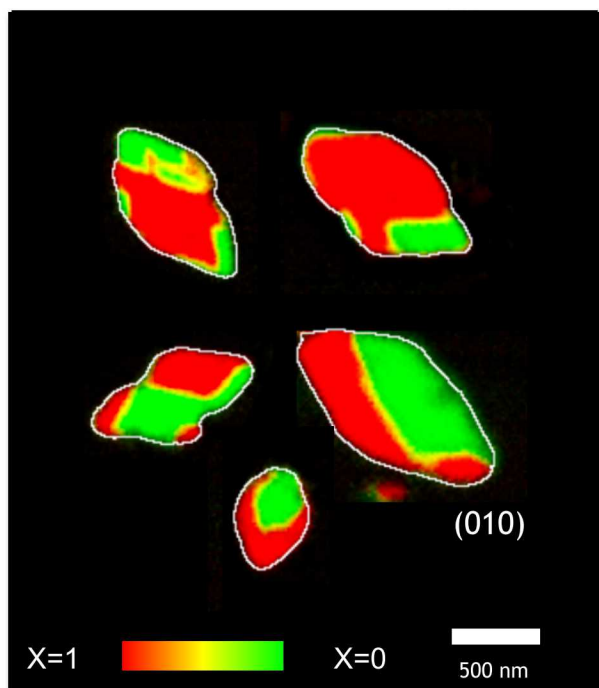
Tracking lithium insertion within particles *in situ*



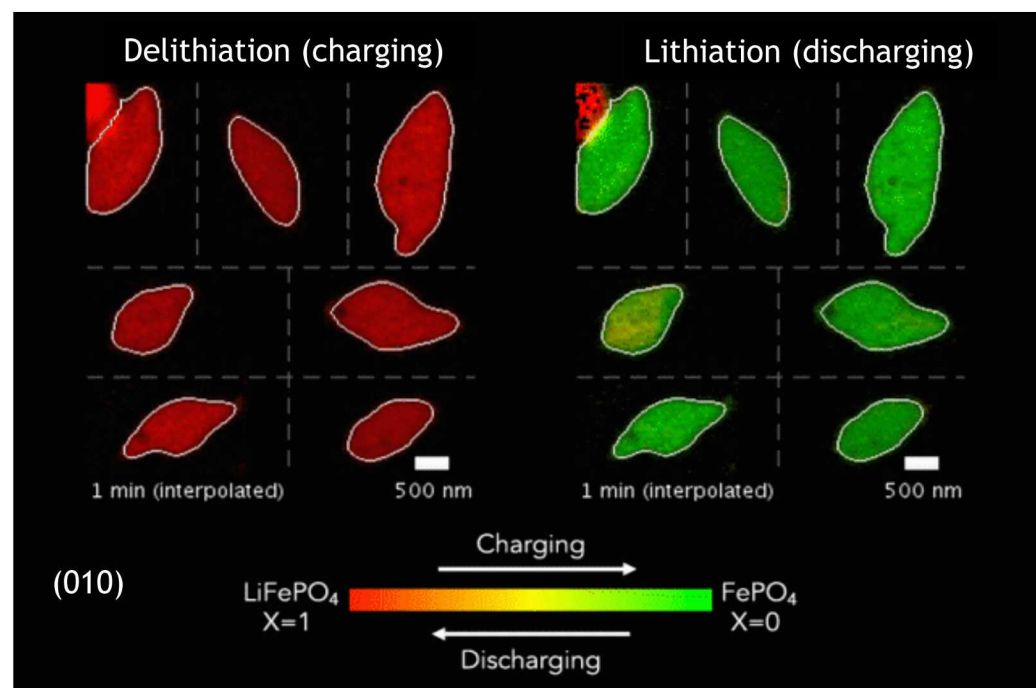
100-nm thick single crystalline particles



One dimensional lithium conductor



Equilibrium & slow rates

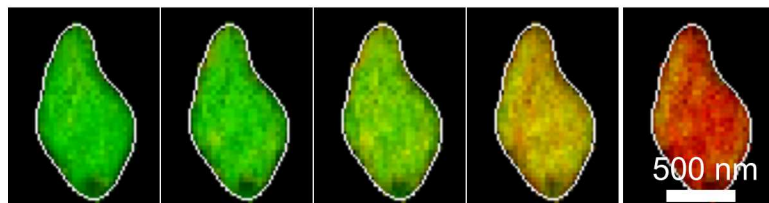


Nonequilibrium lithium insertion



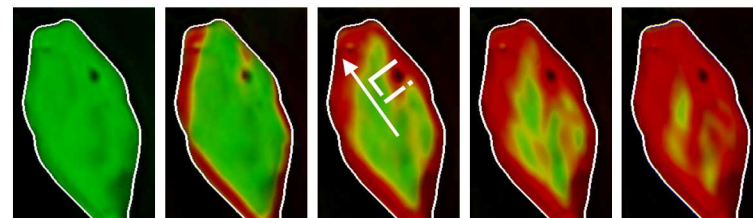
How do we prevent phase separation?

Solid solution



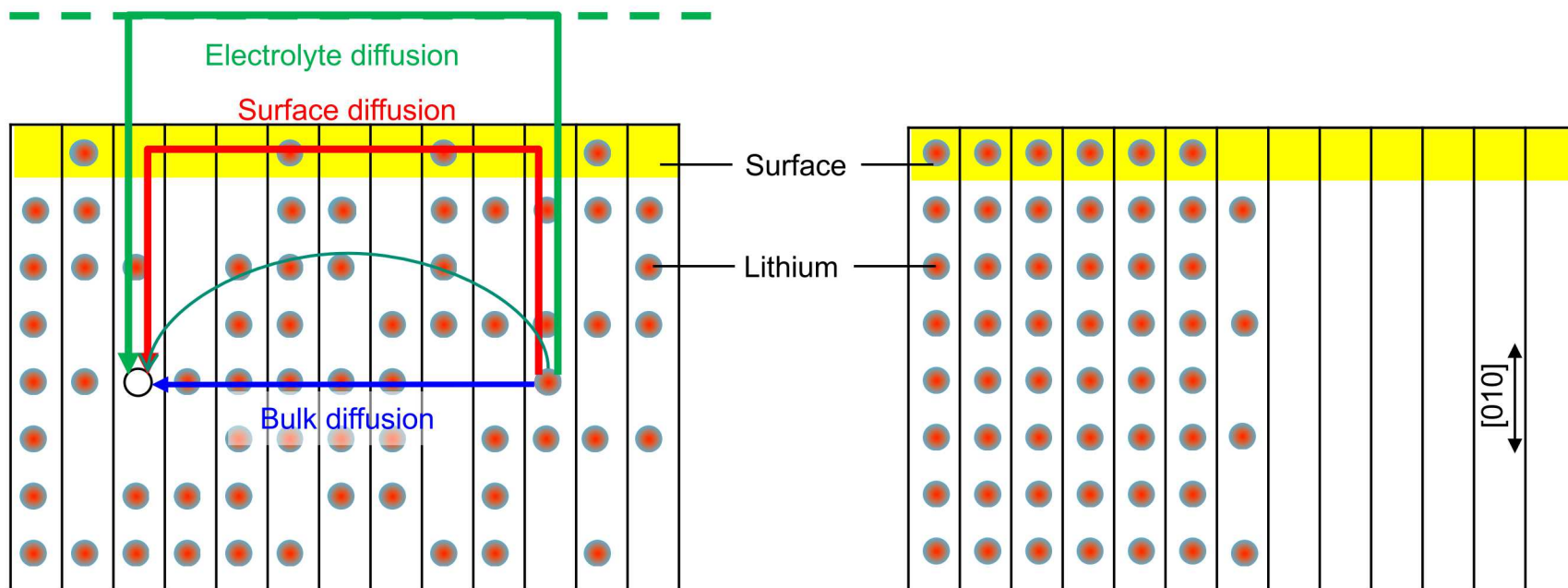
30 min lithiation

Phase separation



7 hour lithiation

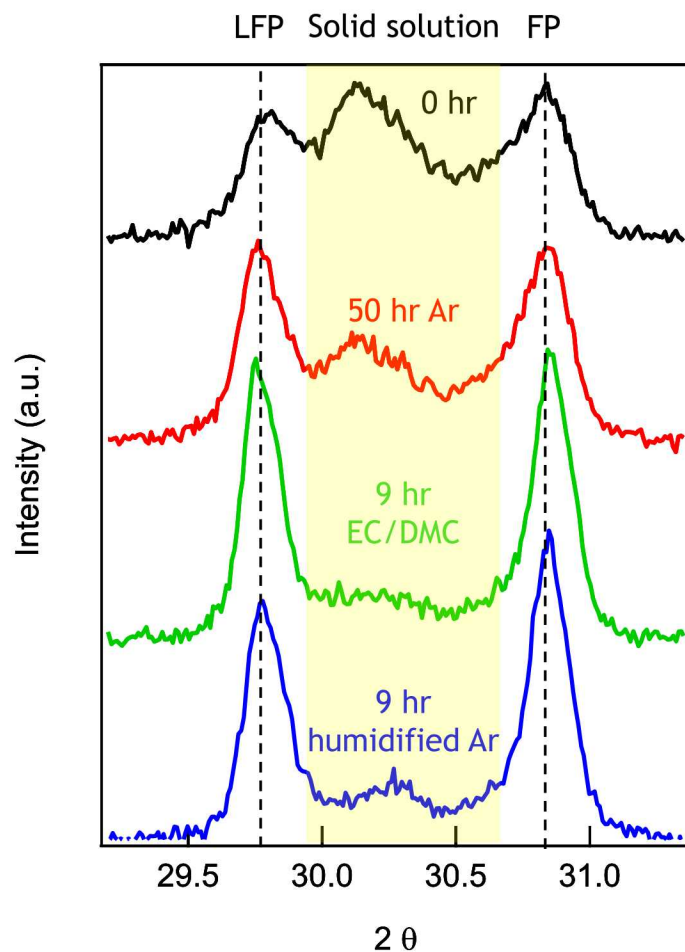
Lithium must diffuse along the non-conducting directions for phase separation



How do we prevent lithium from migrating between channels?

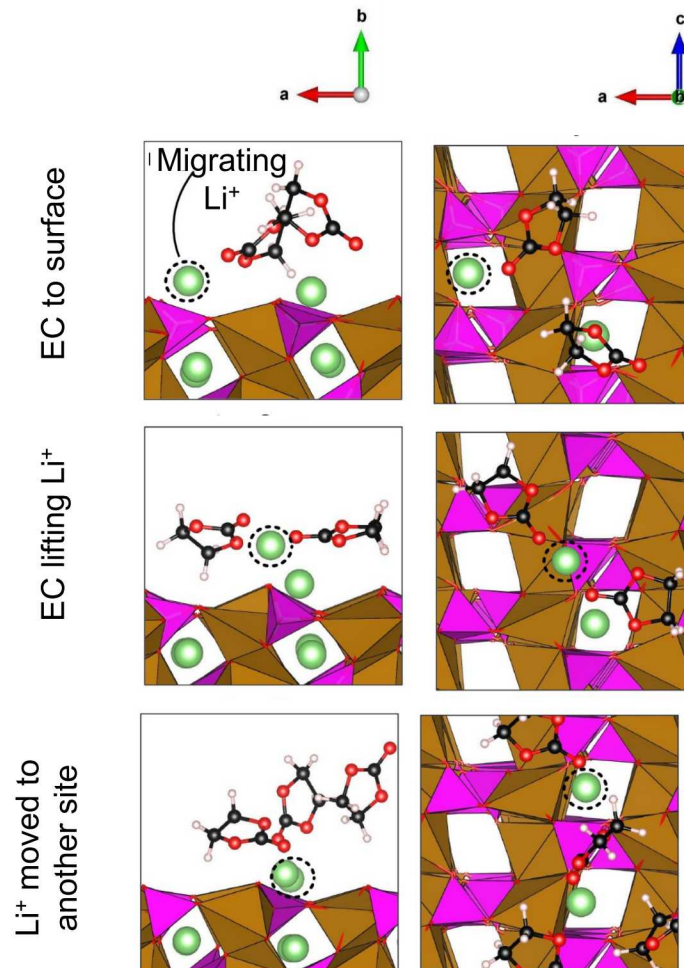


Lithium migration pathway



Fluid molecules enhance phase separation rate.
Lithium migrates at the surface

Li, Chen, Islam, Bazant, Chueh et al. submitted



MD shows solvent-assisted lithium migration

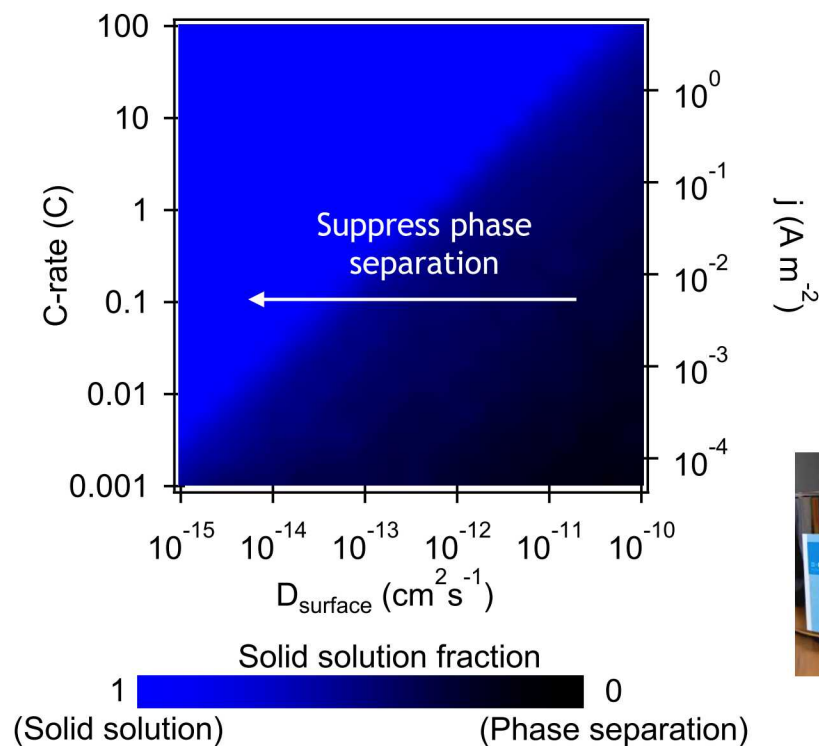
Collaboration: Hungru Chen & Saiful Islam, Univ of Bath



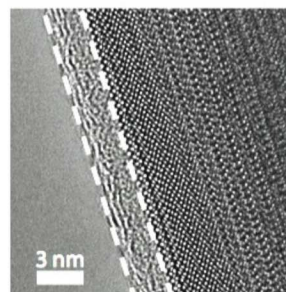
Surface diffusion controls phase separation

Cahn-Hilliard: $\frac{\partial X}{\partial t} = \nabla \left[\frac{D}{k_B T} X(1-X) \nabla \mu_{Li} \right] + j(X, \mu_{Li})$

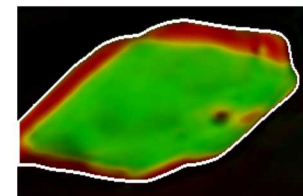
$$\mu_{Li} = \Omega(X)(1-X) + k_B T \ln \frac{X}{1-X} - \kappa \nabla^2 X + \dots$$



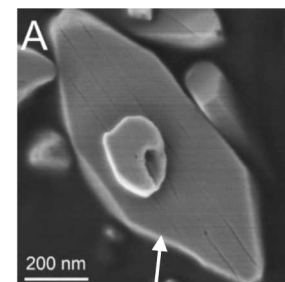
Coating



Phase boundary:
2-4% lattice mismatch
>1 GPa stress



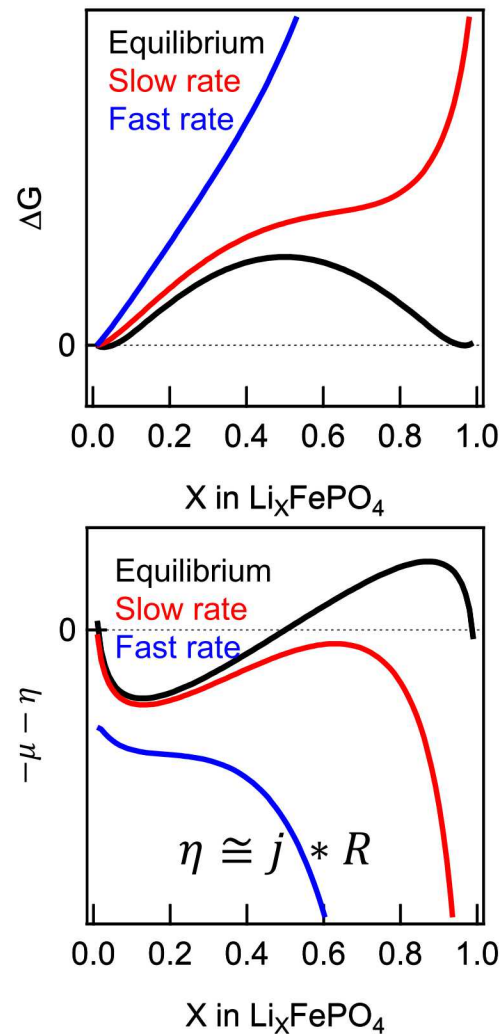
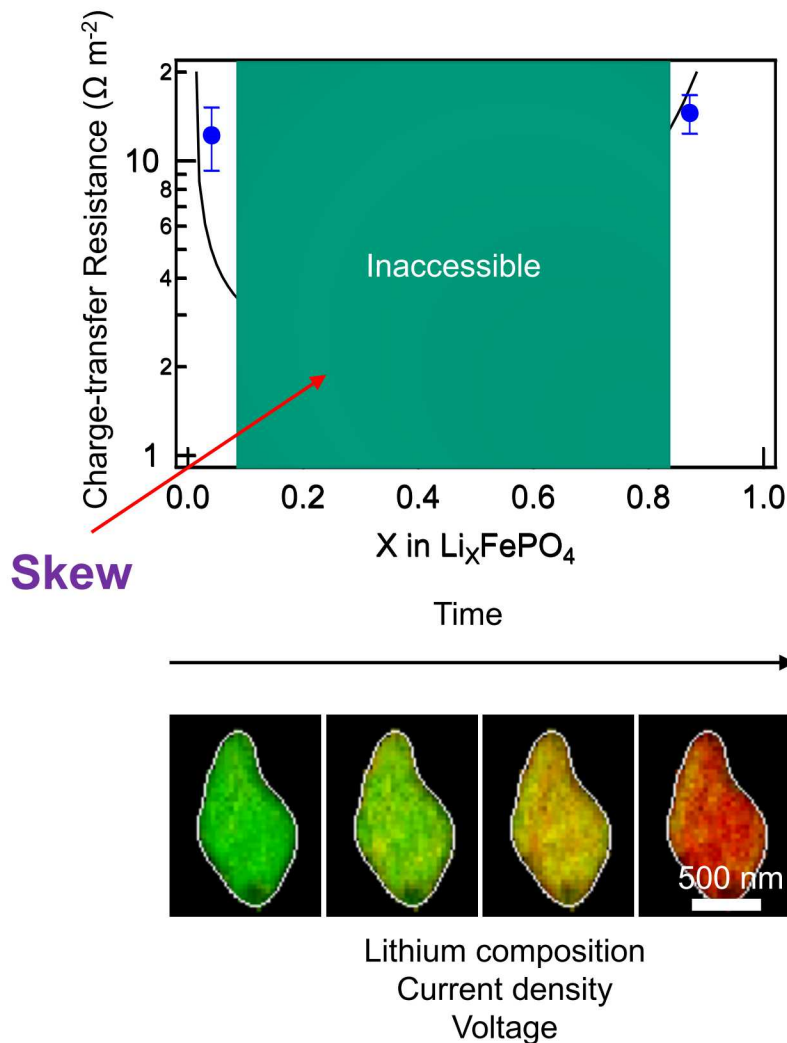
Yu et al. *Nano Lett.* (2015)



Cracks



Interfacial reaction controls bulk thermodynamics

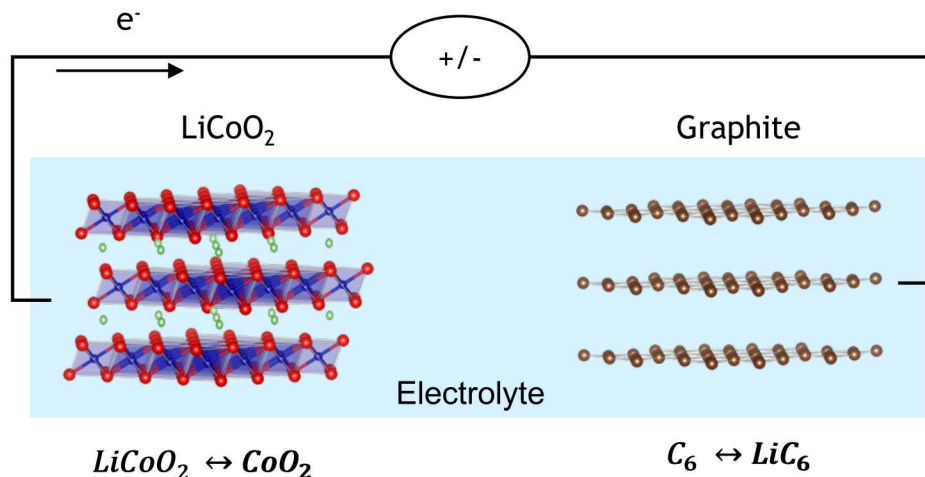


This shape of the resistance suppresses the driving force for phase separation

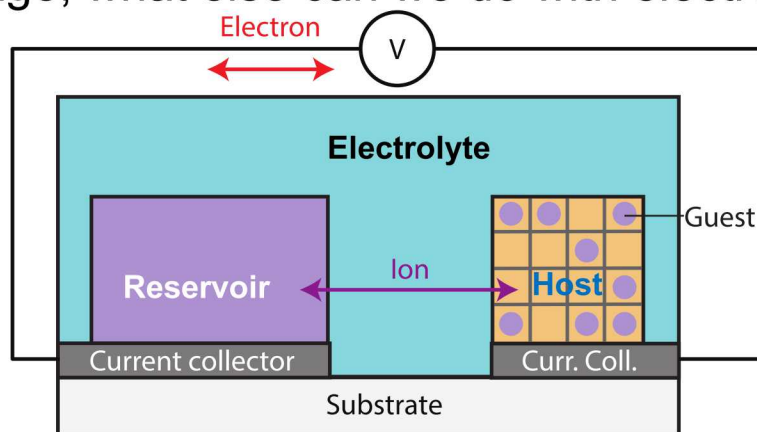


Electrochemical ion insertion

Modify chemical stoichiometry and conduct solid-state chemistry using current and voltage



Beyond energy storage, what else can we do with electrochemical ion insertion?





Artificial neural networks and deep learning

Computers are really fast and efficient at task-specific programming

$$\frac{dx}{dt} = x^2$$

```
x=1;
dt = 0.01;
for i = 1:1000 {
    dxdt = x.^2;
    xnew = dt*dxdt;
    x = xnew; }
end
```

Computers struggle when there are no clear instructions for the task

Which one of these images is a cat?



Image recognition, online advertisement, autonomous driving

Artificial neural networks: how can a machine learn to do an operation through repeated training?

Solution: conduct matrix multiplications, while tuning the weights of the matrix

$$\begin{bmatrix} y_1 \\ \vdots \\ y_m \end{bmatrix} = \begin{bmatrix} w_{1,1} & \cdots & w_{1,n} \\ \vdots & \ddots & \vdots \\ w_{m,1} & \cdots & w_{m,n} \end{bmatrix} \begin{bmatrix} x_1 \\ \vdots \\ x_n \end{bmatrix}$$

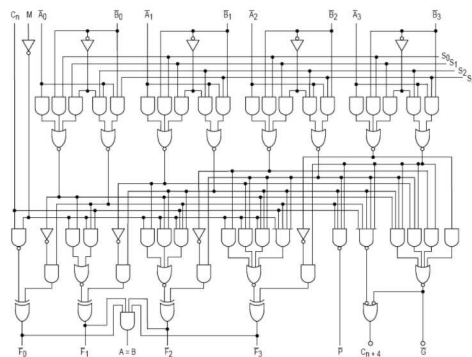


Digital vs analog computation

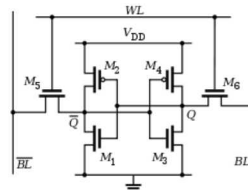
$$\begin{bmatrix} y_1 \\ \vdots \\ y_m \end{bmatrix} = \begin{bmatrix} w_{1,1} & \cdots & w_{1,n} \\ \vdots & \ddots & \vdots \\ w_{m,1} & \cdots & w_{m,n} \end{bmatrix} \begin{bmatrix} x_1 \\ \vdots \\ x_n \end{bmatrix}$$

Digital logic

Arithmetic logic unit for multiplication (read)



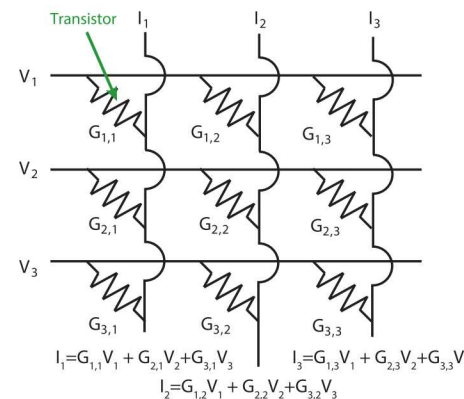
SRAM to store the weights (write)



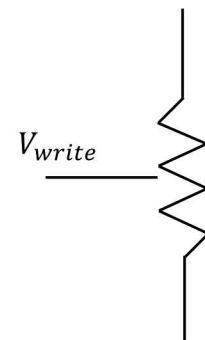
Uses established CMOS technology

Analog logic

Crossbar for matrix multiplication



Modulate conductance during training



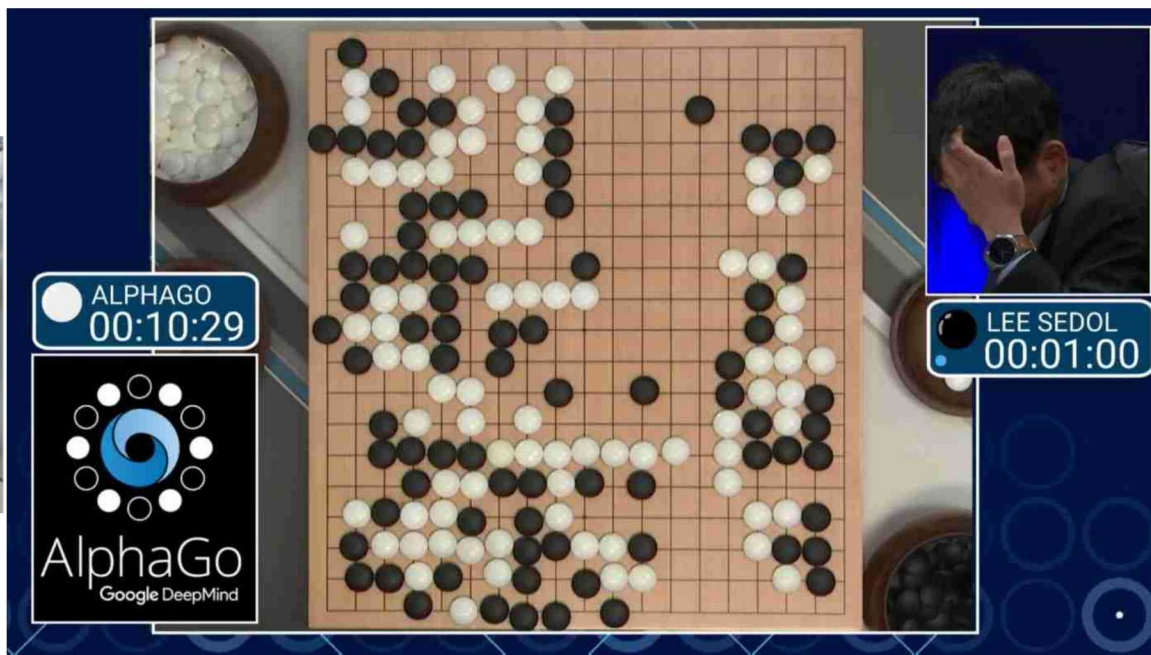
Low power
High parallelism
Simultaneous logic and memory



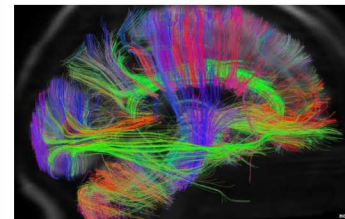
AlphaGo (digital) vs. Lee Sedol (analog)



64 GPU
19 CPU
4 TPU



the brain ~10 Hz



100 billion neurons
100 trillion synapses

AlphaGO: Megawatts

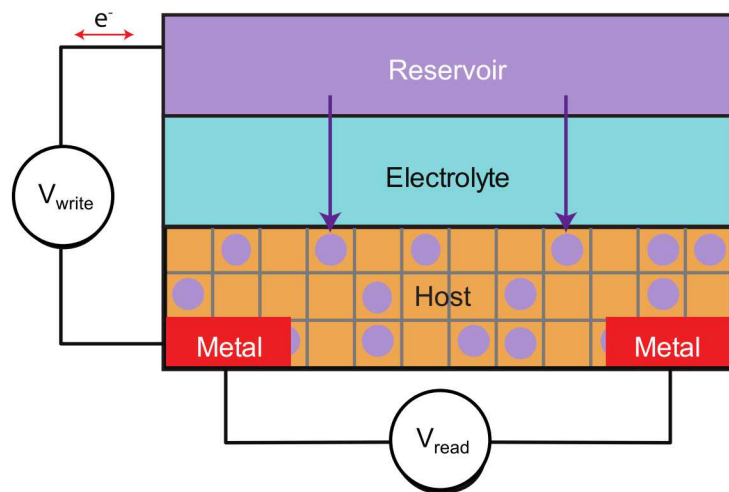
Human brain: 20 watt





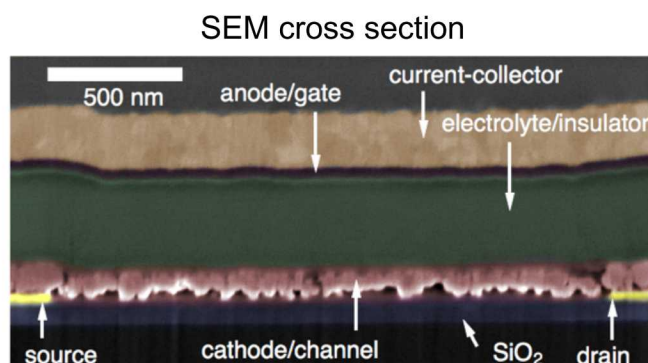
Ion insertion, non-volatile redox transistor

Non-volatile tuning of electronic conductance (weight)



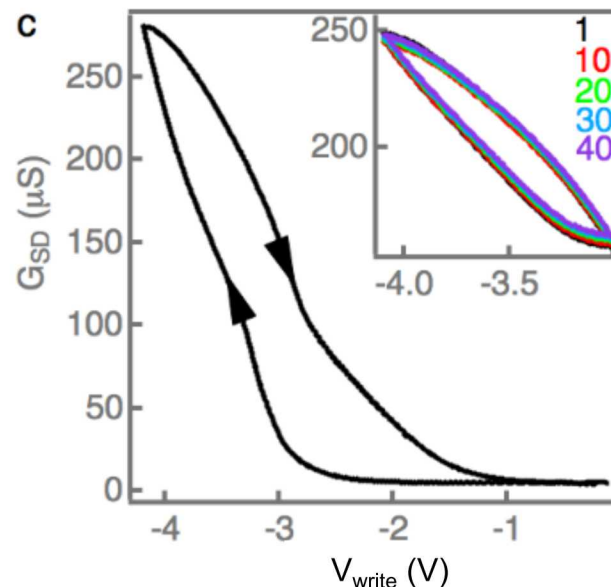
Modulating conductance via doping
n-type: $x Li^+ + xe^- + WO_3 \leftrightarrow Li_xWO_3$
p-type: $LiCoO_2 \leftrightarrow Li_{1-x}CoO_2 + xLi^+ + xe^-$

Li, Chueh. Ann. Rev. Mater. Res. In press



channel electrode: Li_xCoO_2
gate electrode: Li_xSi
solid electrolyte: LiPON

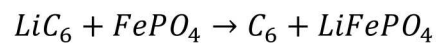
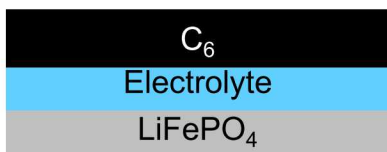
Nonzero open-circuit voltage
High voltage swing





Zero-volt ion insertion transistor

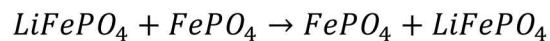
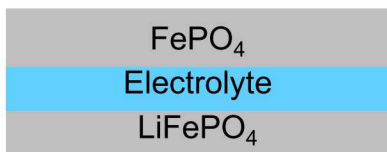
Standard battery: Different lithium hosts



$$\Delta G = -320 \frac{\text{kJ}}{\text{mol}}$$

$$V = -\frac{\Delta G}{nFe} = 3.4 \text{ V}$$

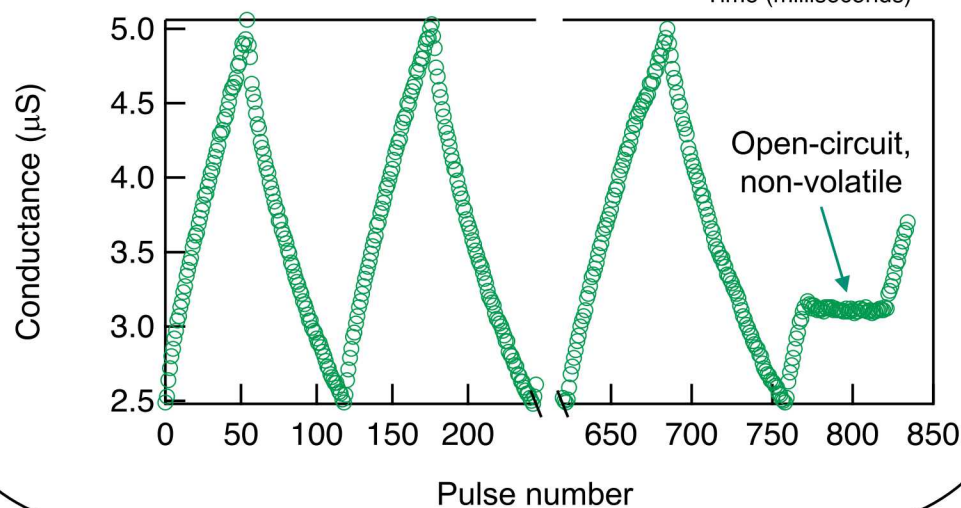
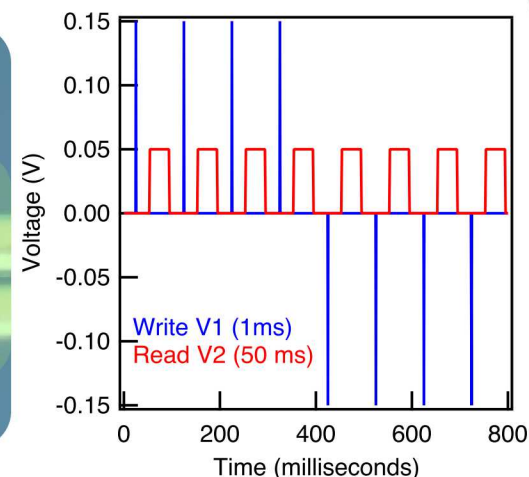
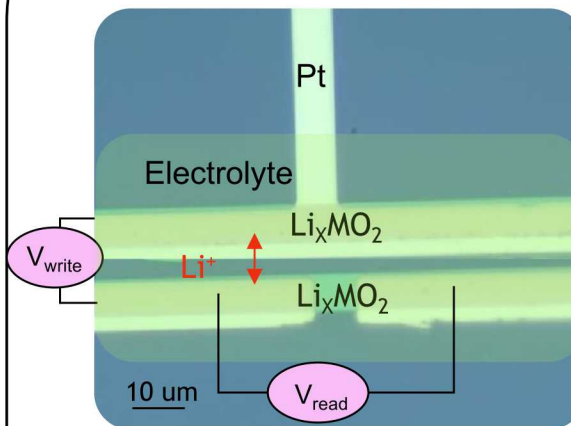
Symmetric battery: Same lithium hosts



$$\Delta G \sim 0 \text{ kJ/mol}$$

$$V \sim 0 \text{ V}$$

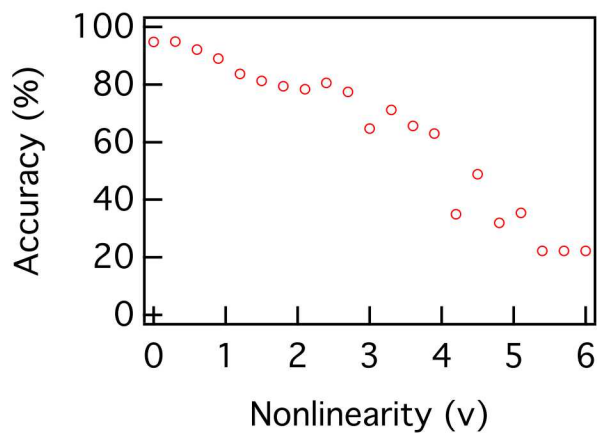
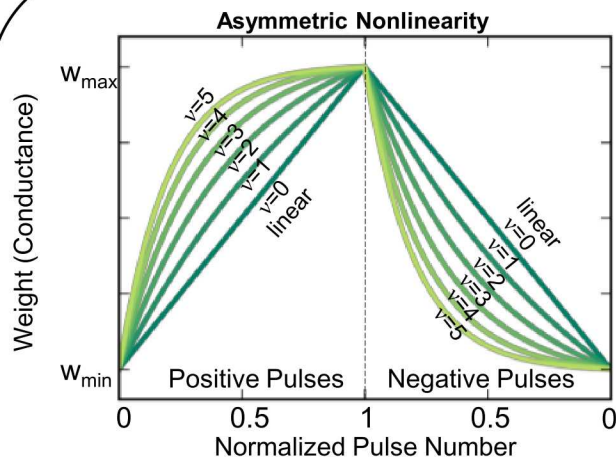
Symmetric battery = zero-voltage transistor





Ion insertion offers high linearity at low write voltages

Linear response allows more accurate and predictable updating of the weights



S. Agarwal et al. *IJCNN*, 2016

$$\begin{bmatrix} y_1 \\ \vdots \\ y_m \end{bmatrix} = \begin{bmatrix} w_{1,1} & \cdots & w_{1,n} \\ \vdots & \ddots & \vdots \\ w_{m,1} & \cdots & w_{m,n} \end{bmatrix} \begin{bmatrix} x_1 \\ \vdots \\ x_n \end{bmatrix}$$

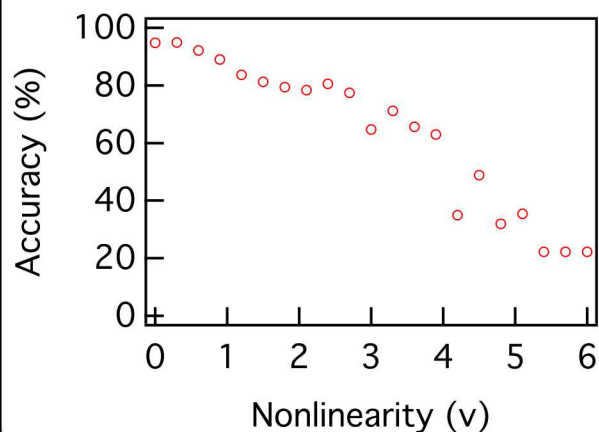
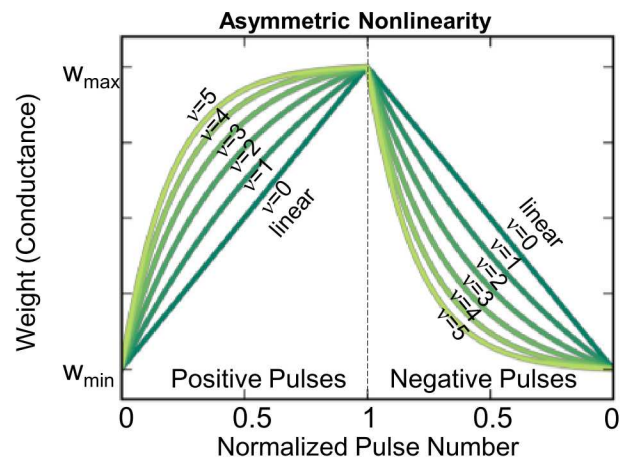


Linearity ensures each w can be tuned by a predictable amount.



Ion insertion offers high linearity at low write voltages

Linear response allows more accurate and predictable updating of the weights

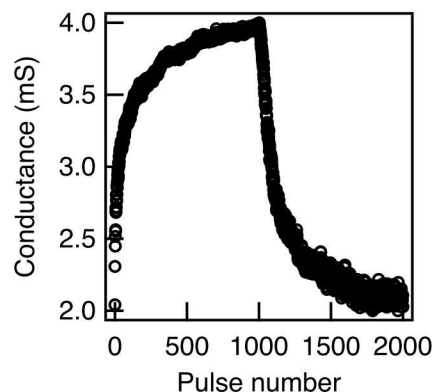


S. Agarwal et al. *IJCNN*, 2016

TaO_x Memristor, ± 1 V

$\nu = 4.9$

Accuracy: $\sim 60\%$

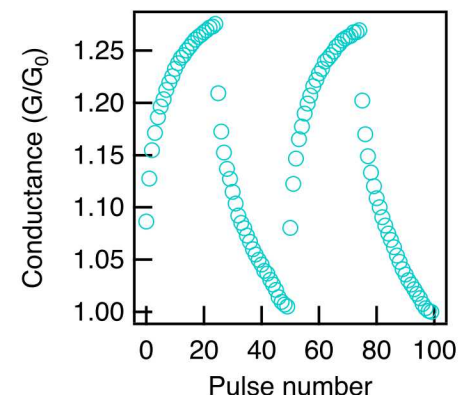


R. Jacobs-Gedrim et al. *ICRC*, 2017

SONOS Flash, ± 9 V

$\nu = 3.7$

Accuracy: $\sim 70\%$

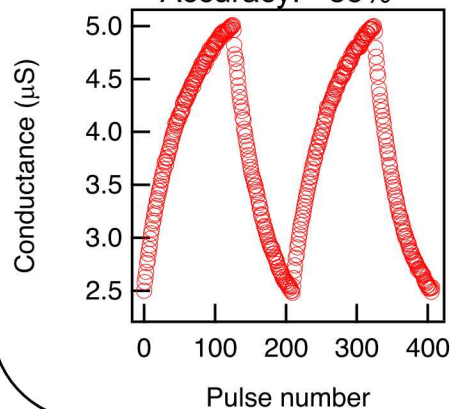


Ion insertion electrode

± 50 mV

$\nu = 2.27$

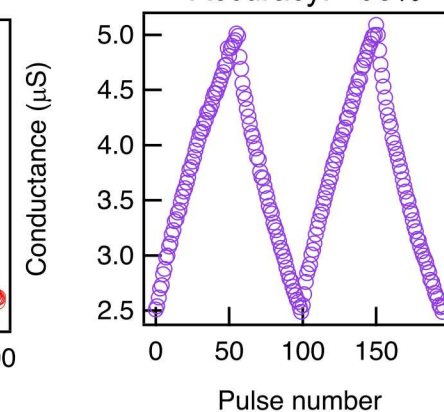
Accuracy: $\sim 85\%$



± 200 mV

$\nu = 0.67$

Accuracy: $\sim 95\%$



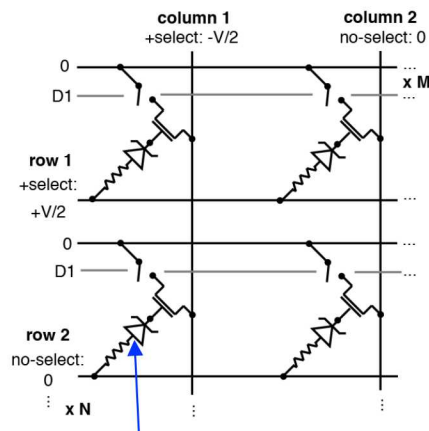
Ion insertion has much higher linearity and much lower power consumption



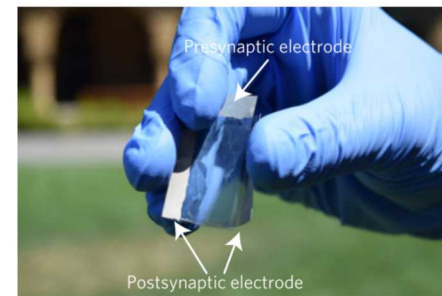
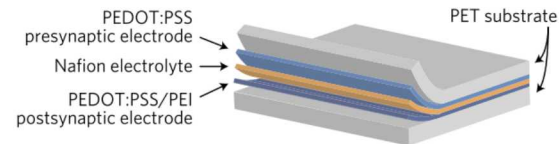
From devices to networks

Can we build a parallel network of redox insertion transistors?

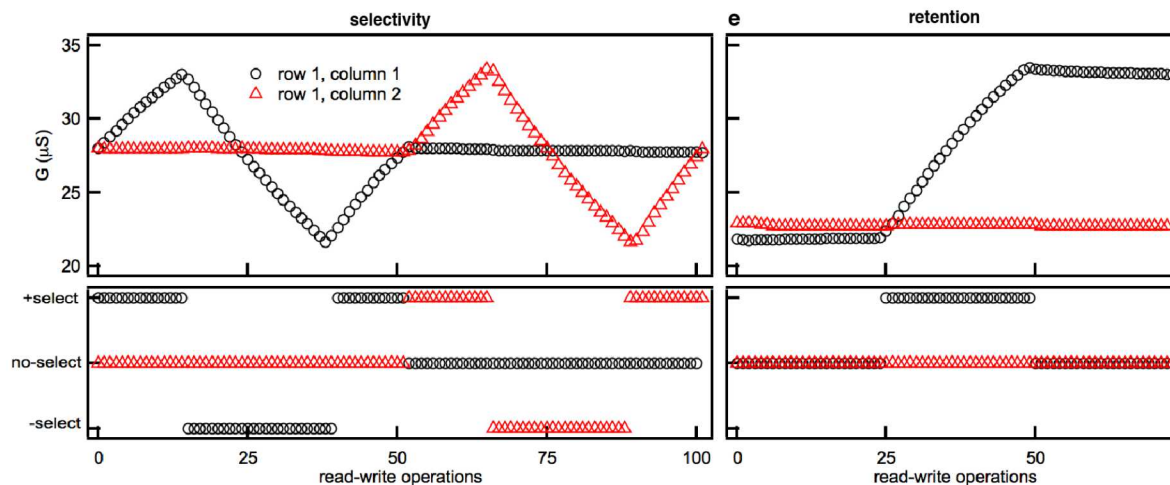
N x M Network



Access device selects certain transistors to write without disturbing others



Polymer-based insertion transistors





Acknowledgements

Stanford

William Chueh

Jongwoo Lim

Will Gent

Norman Jin

Alberto Salleo

Scott Keene

Berkeley Labs

Tolek Tyliszczak

David Shapiro

MIT

Martin Bazant

Dan Cogswell

Sandia

Alec Talin

Elliot Fuller

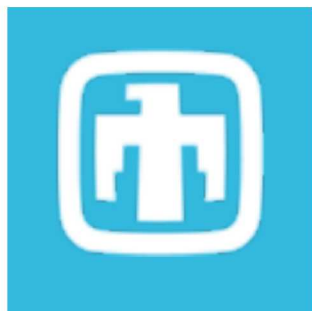
Farid el Gabaly

Sapan Agarwal

Univ of Bath

Martin Bazant

Dan Cogswell



SAMSUNG ADVANCED
INSTITUTE OF TECHNOLOGY

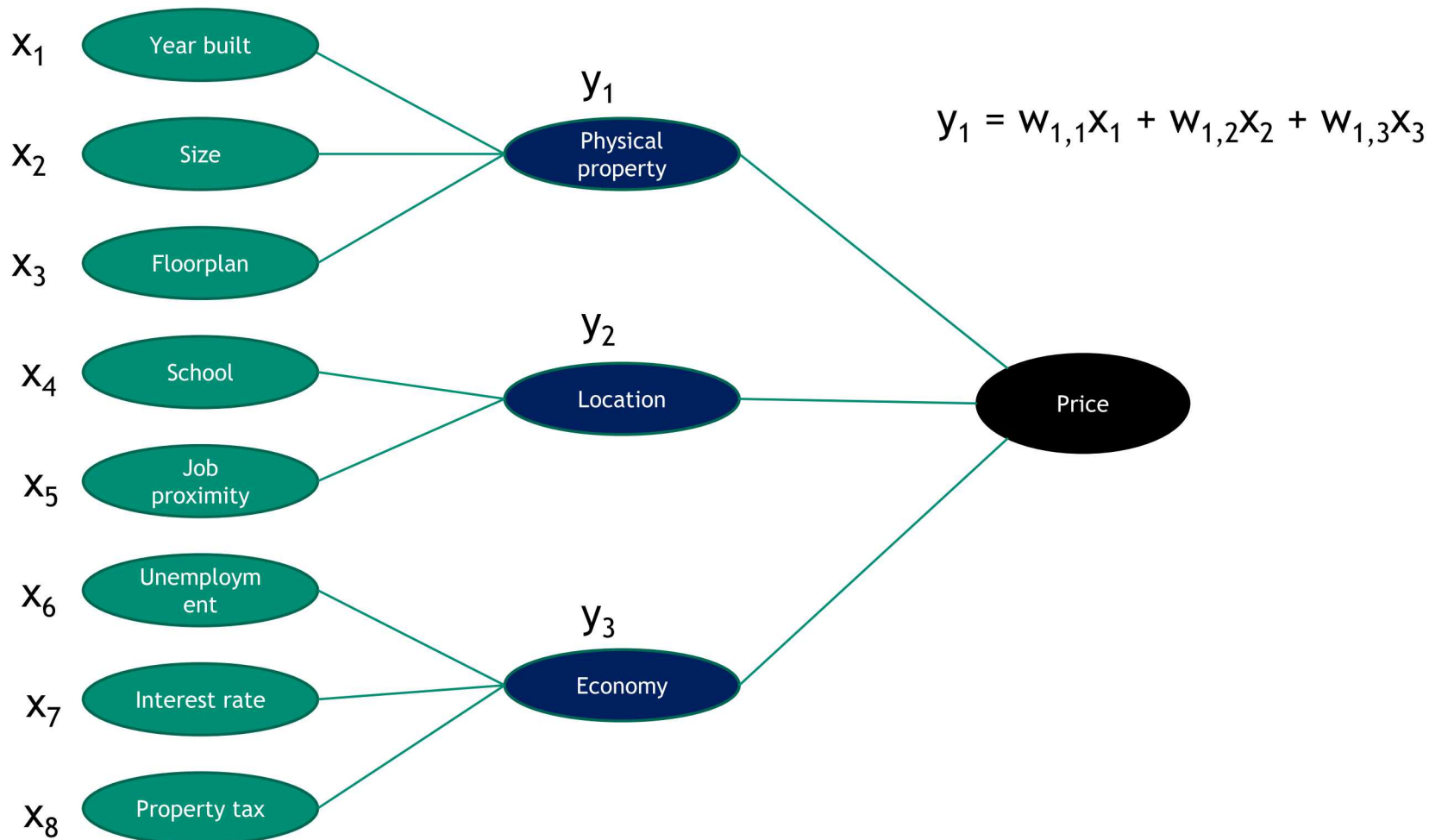


This work is supported by the Sandia National Laboratories Truman Fellowship Program, which is funded by the Laboratory Directed Research and Development (LDRD) Program. Sandia National Laboratories is a multi-mission laboratory managed and operated by National Technology and Engineering Solutions of Sandia, LLC, a wholly owned subsidiary of Honeywell International Inc., for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-NA-0003525.



Matrix multiplication and artificial neural networks

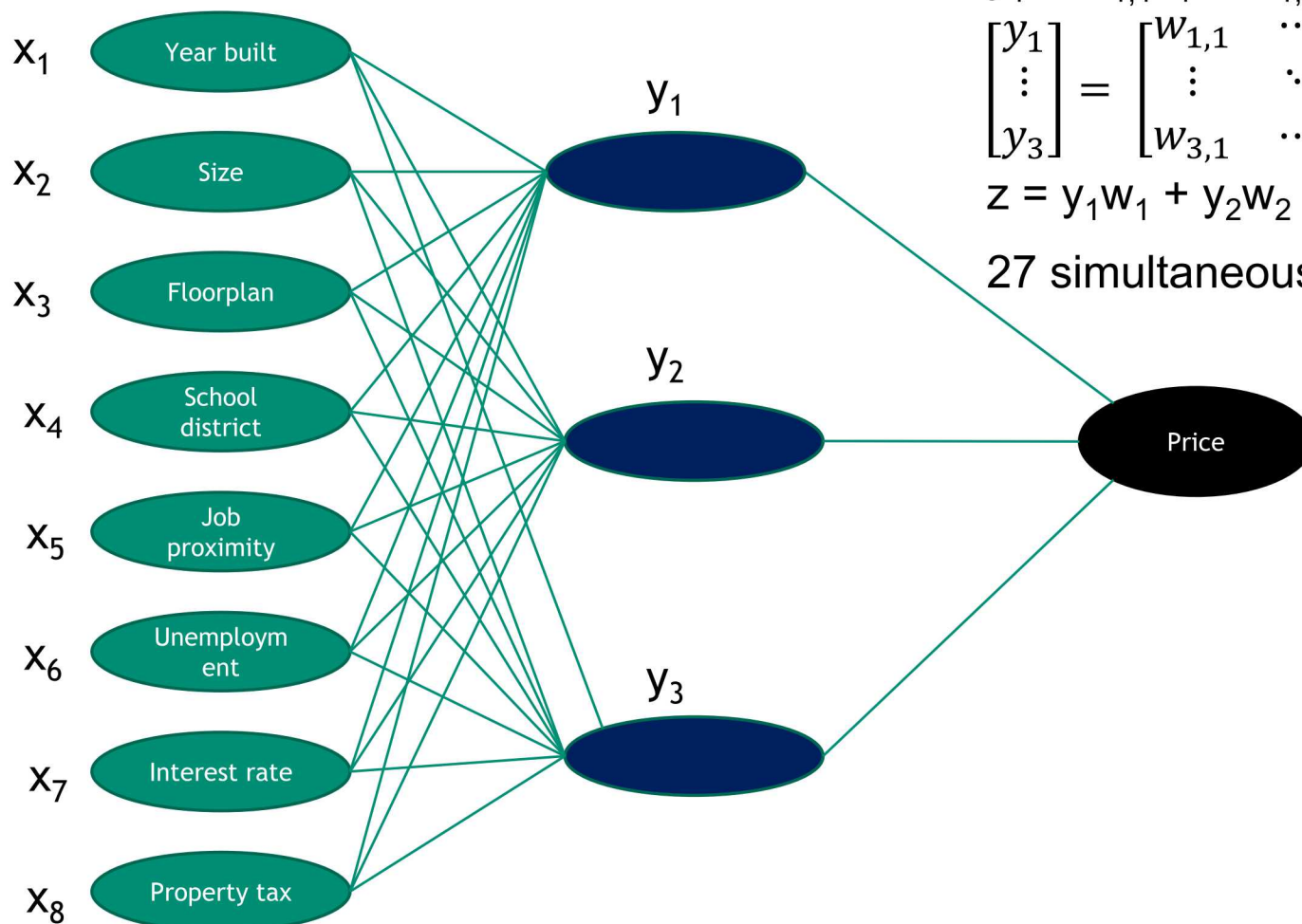
How much is my home worth?





Matrix multiplication and artificial neural networks

How much is my home worth?



$$y_1 = w_{1,1}x_1 + w_{1,2}x_2 + \dots + w_{1,8}x_8$$

$$\begin{bmatrix} y_1 \\ \vdots \\ y_3 \end{bmatrix} = \begin{bmatrix} w_{1,1} & \cdots & w_{1,8} \\ \vdots & \ddots & \vdots \\ w_{3,1} & \cdots & w_{3,8} \end{bmatrix} \begin{bmatrix} x_1 \\ \vdots \\ x_8 \end{bmatrix}$$

$$z = y_1w_1 + y_2w_2 + y_3w_3$$

27 simultaneous multiplication

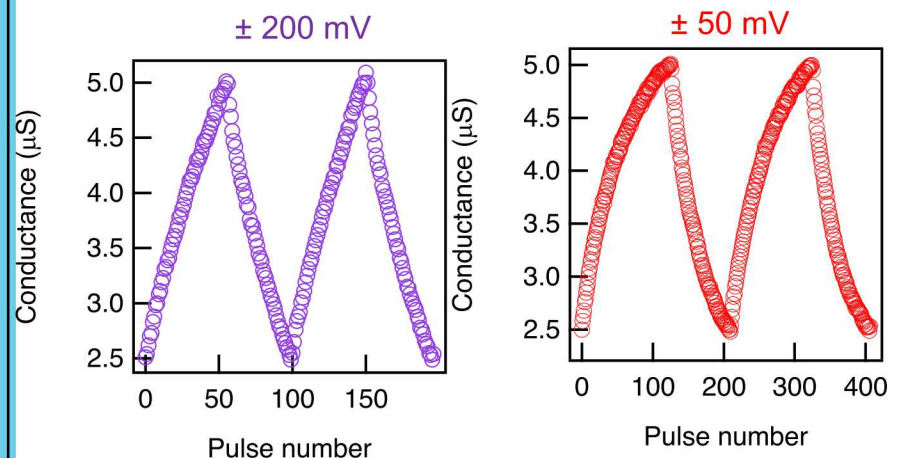
Neural networks often have 100 million weights

Google tensor processor unit does 65k simultaneous multiplications



Voltage pulse and linearity

Why does higher voltage pulses result in more linear response?



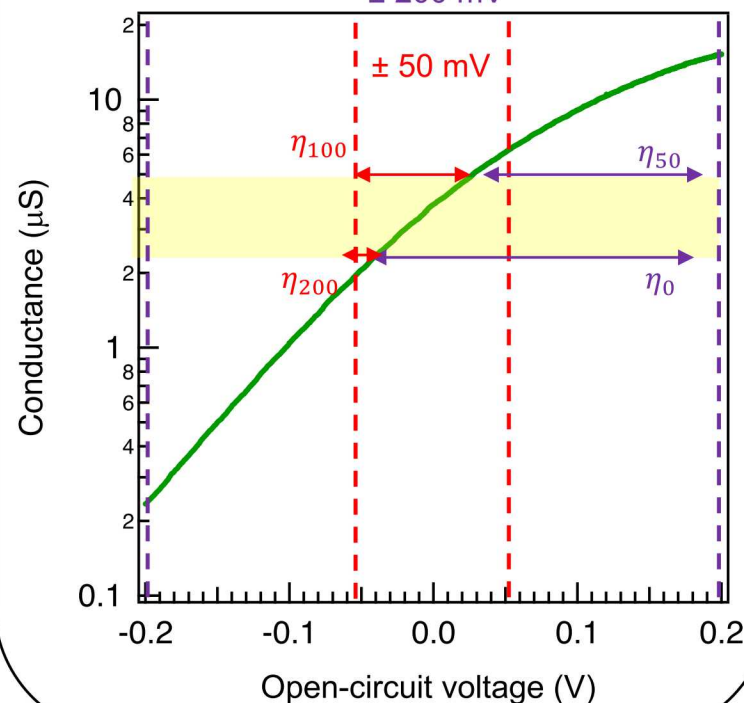
Overpotential decreases **slightly** with pulse number

Overpotential decreases **drastically** with pulse number

The open-circuit potential varies by ~100 mV due to the entropy of lithium

$$\mu = k_b T \ln \frac{x}{1-x}$$

± 200 mV

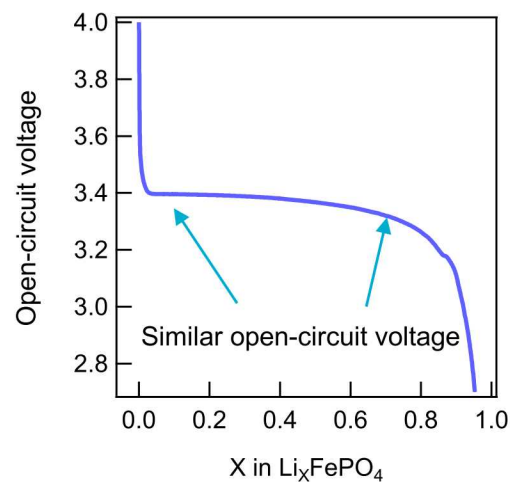
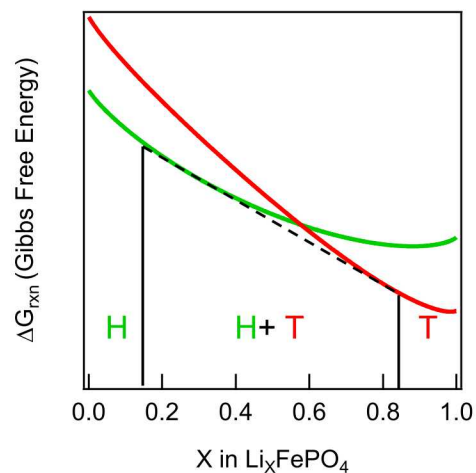


Goal: Find a material with higher dS/dV so the open-circuit voltage does not change with lithium?

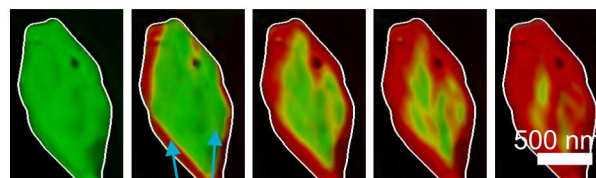


Phase-separation and voltage plateau

Phase separation

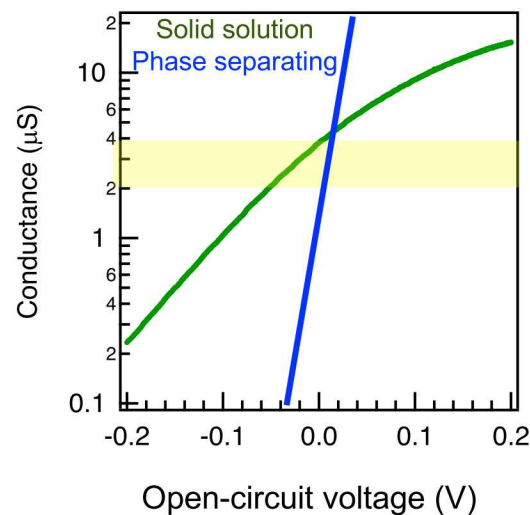


$X=1$ $X=0$



Lithium insertion

Different lithium doping concentrations
Same chemical potential



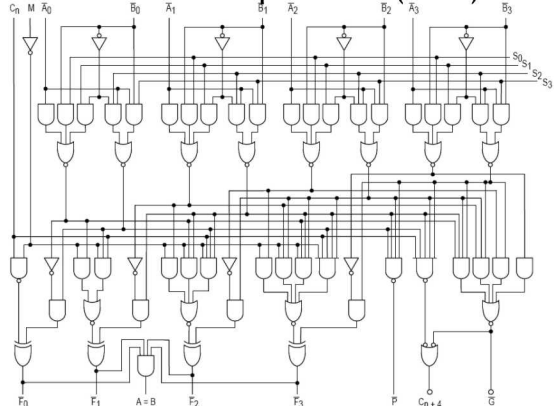


Parallel analog processing

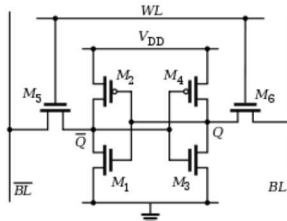
Aim: to mimic the brain and design a low-power device to conduct parallel analog matrix multiplication

Digital logic

Arithmetic logic unit for matrix multiplication (read)

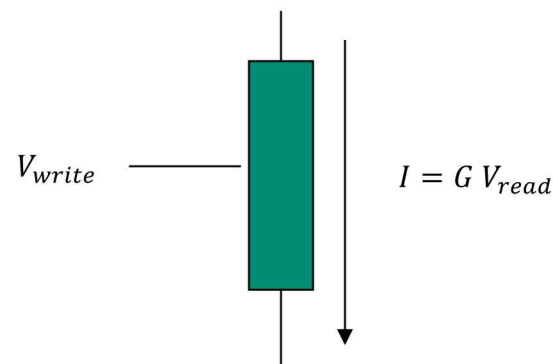


Static RAM for memory of the weights (write)



Analog logic

Computation: modulate G continuously
Memory: G should be non-volatile



$$\text{Power} = C V_{\text{write}}^2$$

Goal: Design devices that can linearly modulate the conductance with analog states, and retain that conductance (non-volatile)